



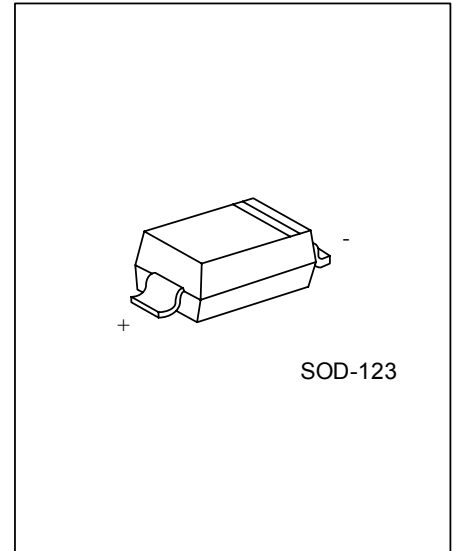
## 1N5819

DIODE

### SCHOTTKY BARRIER DIODE

#### ■ FEATURES

- \* Schottky barrier chip
- \* Low power loss, high efficiency.
- \* Low forward voltage drop.
- \* High surge current capability.
- \* For use in low voltage, high frequency inverters, free wheeling diode, and polarity protection applications.



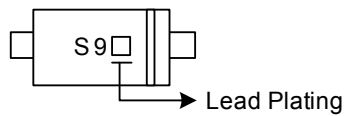
\*Pb-free plating product number: 1N5819L

#### ■ ORDERING INFORMATION

Order Number		Package	Packing
Normal	Lead Free Plating		
1N5819-CA2-R	1N5819L-CA2-R	SOD-123	Tape Reel

<p>1N5819L-CA2-R</p> <p>(1)Packing Type (2)Package Type (3)Lead Plating</p>	<p>(1) R: Tape Reel (2) CA2: SOD-123 (3) L: Lead Free Plating Blank: Pb/Sn</p>
---	--

#### ■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (Single Diode @T<sub>A</sub>=25 )

PARAMETER	SYMBOL	RATINGS	UNIT
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	40	V
Maximum non-repetitive Peak Reverse Voltage	V <sub>RM</sub>	40	V
Maximum DC Blocking Voltage	V <sub>R</sub>	40	V
Working Peak Reverse Voltage	V <sub>RWM</sub>	40	V
Maximum RMS Reverse Voltage	V <sub>R(RMS)</sub>	28	V
Repetitive Peak Forward Current	I <sub>FRM</sub>	625	mA
Non-repetitive Peak Forward Surge Current 8.3ms Single Half-Sine-Wave	I <sub>FSM</sub>	25	A
Average Forward Rectified Output Current	I <sub>OUT</sub>	1	A
Power Dissipation	P <sub>D</sub>	250	mW
Storage Temperature Range	T <sub>STG</sub>	-65~+150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

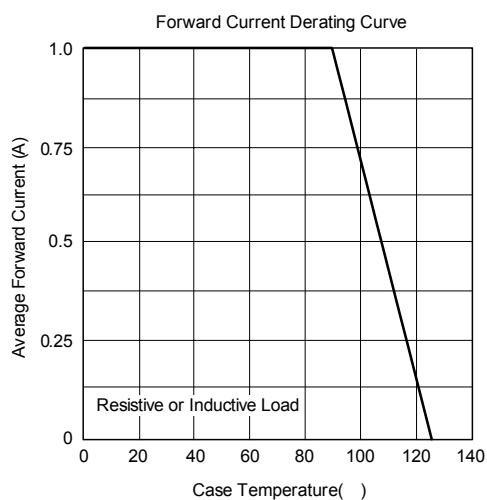
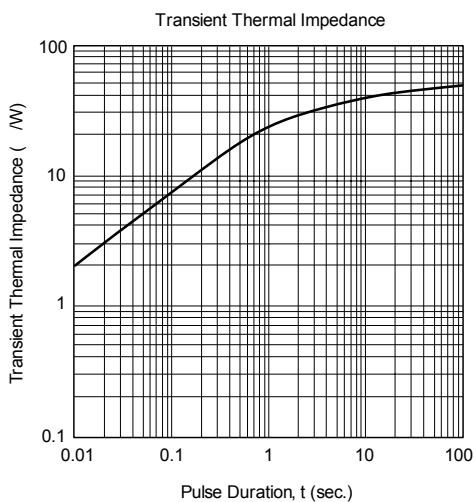
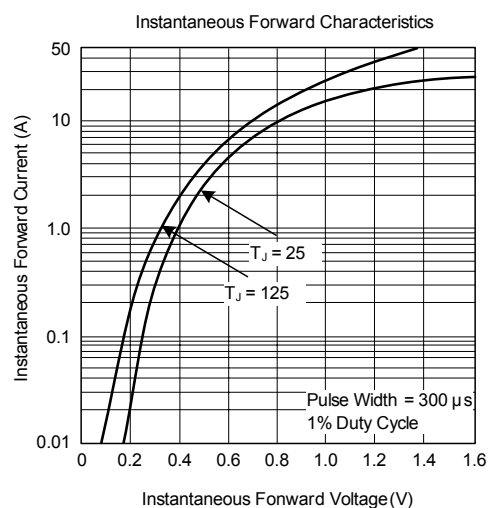
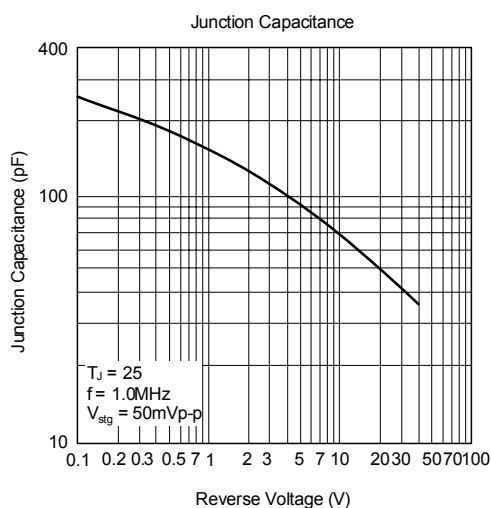
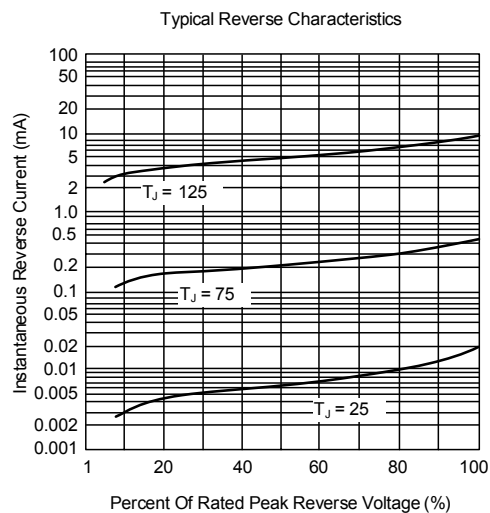
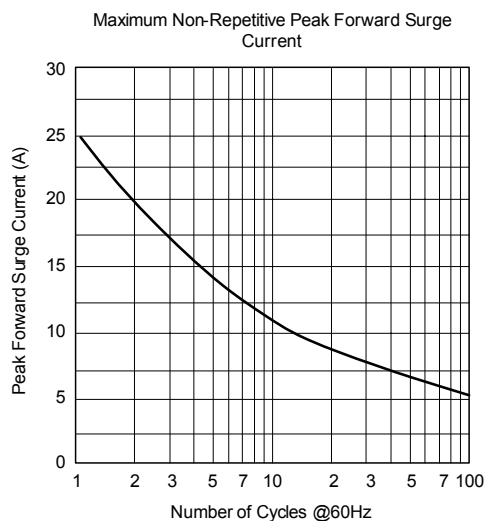
■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Ambient Resistance Junction to Ambient	θ <sub>JA</sub>	500	/W

■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25 , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =1A			0.6	V
		I <sub>F</sub> =3A			0.9	V
Reverse Breakdown Voltage	BV <sub>R</sub>	I <sub>R</sub> = 1mA	40			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> =40V			1	mA
Diode Capacitance	C <sub>D</sub>	V <sub>R</sub> =4V, f=1MHz			120	pF

# TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.